

Journals

- (1) A. K. Shringi, A. Betal, S. Sahu, and M. Kumar, "Write-once-read-many-times resistive switching behavior of amorphous barium titanate based device with very high on-off ratio and stability," *Appl. Phys. Lett.*, vol. 118, no. 26, p. 263505, 2021.
- (2) A. K. Shringi, A. Betal, S. Sahu, and M. Kumar, "Temperature induced low voltage write-once-read-many resistive switching in Ag/BTO/Ag thin films," *J. Mater. Sci. Mater. Electron.*, pp. 1–10, 2022.
- (3) A. K. Shringi, A. Betal, S. Sahu, M. Saliba, and M. Kumar, "Resistive Switching and Synaptic Behavior of Perovskite Lanthanum Orthoferrite Thin Film for Neuromorphic Computing," *IEEE Trans. Electron Devices*, 2022.
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- (5) M. Das, A. K. Shringi, and M. Kumar, "MoS₂ Decorated α -Fe₂O₃ Nanostructures for Efficient NO₂ Gas Sensor," *IEEE Sens. J.*, vol. 22, no. 20, pp. 19183–19190, 2022.
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- (7) V. Raghuwanshi, D. Bharti, A. K. Mahato, A. K. Shringi, I. Varun, and S. P. Tiwari, "High performance flexible organic field-effect transistors with barium strontium titanate gate dielectric deposited at room temperature," *ACS Appl. Electron. Mater.*, vol. 2, no. 2, pp. 529–536, 2020.

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